

WSB5511M

3A Schottky Barrier Diode

[Http://www.sh-willsemi.com](http://www.sh-willsemi.com)

Features

- Low forward voltage
- Extremely low thermal resistance
- High current capability



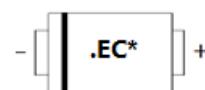
SMA (DO-214AC)



Applications

- Switching circuit
- Middle current rectification

Circuit



Marking

Absolute maximum ratings

Parameter	Symbol	Value	Unit
Reverse voltage (repetitive peak)	V_{RRM}	40	V
Reverse voltage (DC)	V_R	40	V
Average rectified forward current (DC)	I_O	3.0	A
Forward Peak Surge Current ⁽¹⁾	I_{FSM}	50	A
Junction temperature	T_J	-55 ~ 150	°C
Operating temperature	T_{opr}	-55 ~ 150	°C
Storage temperature	T_{stg}	-55 ~ 150	°C

Electronics characteristics ($T_A=25^\circ C$)

Parameter	Symbol	Condition	Min.	Typ.	Max.	Unit
Forward voltage ⁽²⁾	V_F	$I_F=3.0A$			0.50	V
Reverse current	I_R	$V_R=40V$			0.5	mA
Junction capacitance	C_J	$V_R=4V, F=1MHz$		220		pF
Thermal resistance	$R_{\theta(J-L)}$	Junction to Lead (Fig.2)		17		K/W

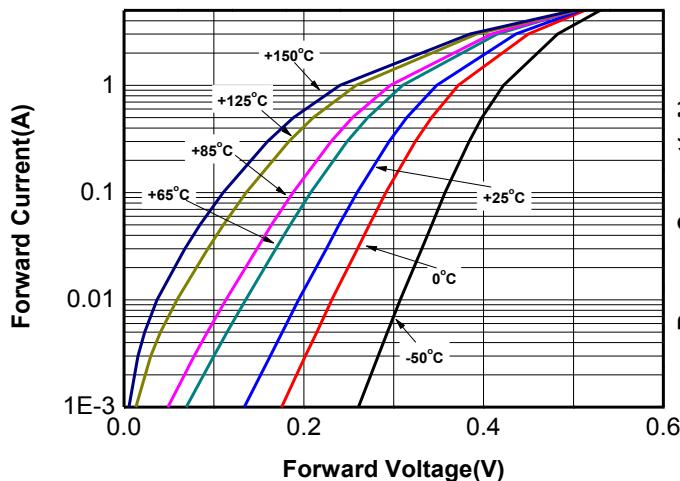
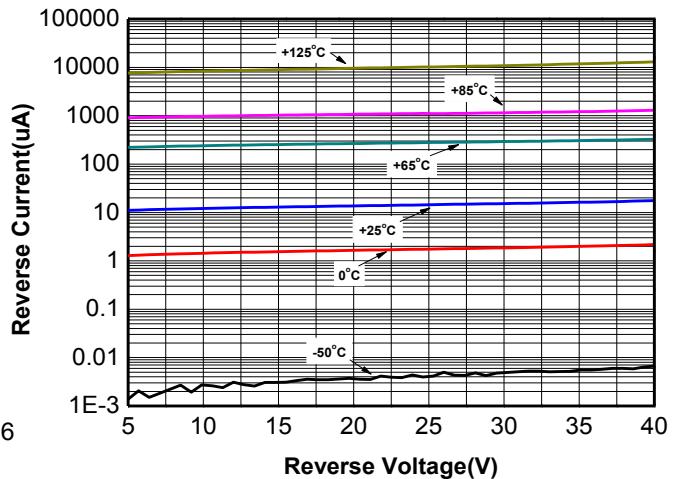
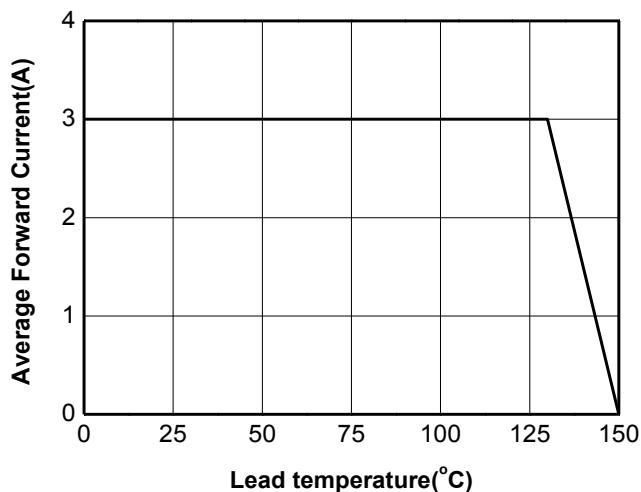
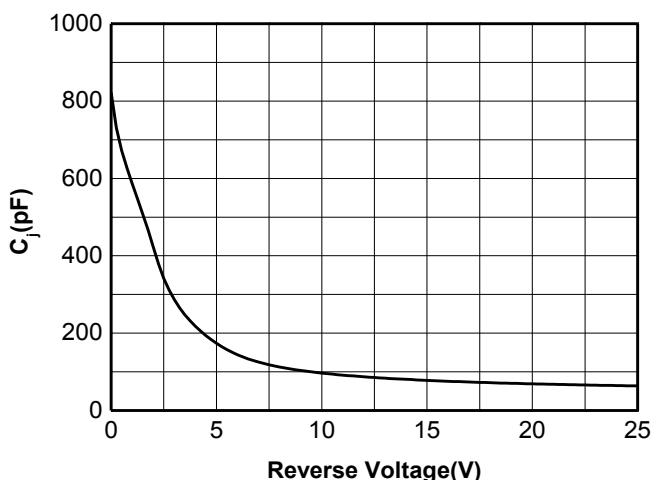
Order Informations

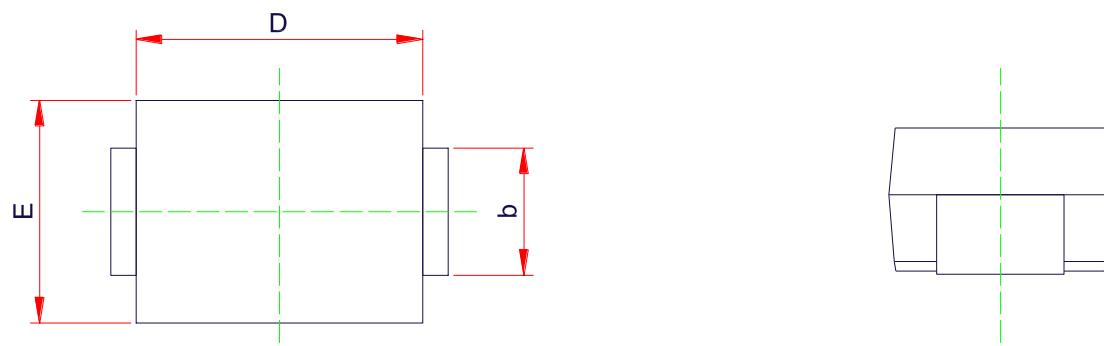
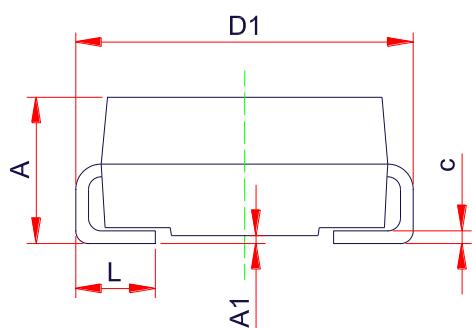
Device	Package	Marking	Shipping
WSB5511M-2/TR	SMA (DO-214AC)	.EC* ⁽³⁾	5000/Reel&Tape

Note1: Pulse width=8.3ms, single pulse;

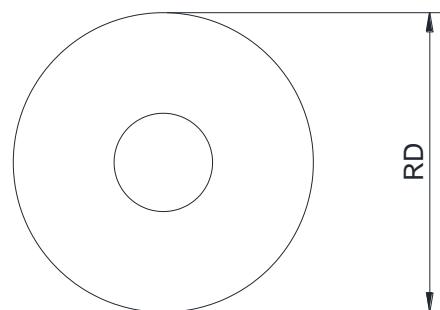
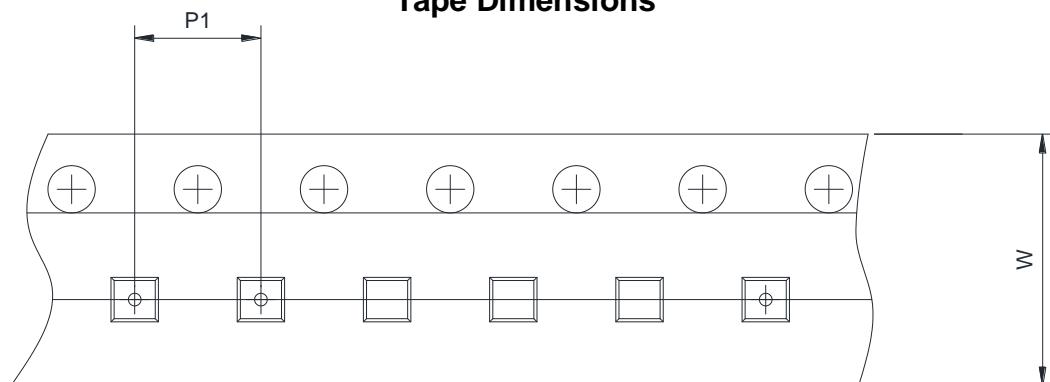
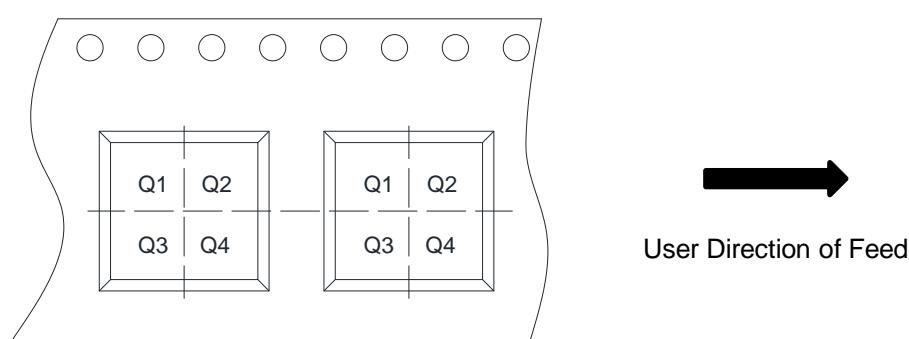
Note2: Single Pulse, test $T_p=380\mu s$;

Note3: * =Month code (A~Z); .EC =Device code;

Typical characteristics (Ta=25°C, unless otherwise noted)

Fig.1 Forward voltage vs. Forward current

Fig.2 Reverse current vs. Reverse voltage

Fig.3 Maximum Forward Current Derating Curve

Fig.4 Junction capacitance vs. Reverse voltage

Package outline dimensions
SMA

TOP VIEW
SIDE VIEW

SIDE VIEW

Symbol	Dimensions in millimeters	
	Min.	Max.
A	1.90	2.50
A1	0.203 MAX	
D	3.90	4.70
D1	4.75	5.35
E	2.40	2.85
c	0.10	0.31
b	1.27	1.95
L	0.76	1.55

TAPE AND REEL INFORMATION
Reel Dimensions

Tape Dimensions

Quadrant Assignments For PIN1 Orientation In Tape


RD	Reel Dimension	<input type="checkbox"/> 7inch	<input checked="" type="checkbox"/> 13inch
W	Overall width of the carrier tape	<input type="checkbox"/> 8mm	<input checked="" type="checkbox"/> 12mm
P1	Pitch between successive cavity centers	<input type="checkbox"/> 2mm	<input checked="" type="checkbox"/> 4mm
Pin1	Pin1 Quadrant	<input checked="" type="checkbox"/> Q1	<input checked="" type="checkbox"/> Q2
		<input type="checkbox"/> Q3	<input type="checkbox"/> Q4

制修订记录				
文件版本	制修日期	修订页次	修订人	变更内容
Rev.1.0	2013/5/21			建立文档
Rev.1.1	2013/7/24			修改 IF=3A
Rev.1.2	2013/8/28			修改 VF 和 IR 曲线, Marking
Rev.1.3	2013/10/08			修改 VF 与 IR, Cj 曲线
Rev.1.4	2014/01/21		衷世雄	添加 125 度曲线
Rev.1.5	2014/03/17		衷世雄	更换 wafer, 相关信息更新
批准		审核		编制 衷世雄
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各部门会签				
应用部	封装部	市场部	生产管理部	